Supplemental

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	8	("4996574"|"6165828"|"6177299"|"6365465").PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/18 15:29
L2	5	(US-6967377-$ or US-5574294-$ or US-6426532-$ or US-6365465-$ or US-5773331-$).did.	USPAT	OR	ON	2007/02/18 15:42
L3	3	("4996574" | "6165828" | "6177299").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/02/18 15:47
L4	3736	M?sfet and substrate and (gate with channel with well)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/18 15:50
L5	410	L4 and (gate with electrical$3 with well)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/18 15:50
L6	83	L5 and ((gate with (connect$3 or contact)) with (well and under and channel))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/18 15:50
L7	48	L6 and body	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/18 15:50
L8	2258	257/347.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/18 16:02
L9	372	257/249.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/18 16:09
L10	1475	257/401.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/18 16:12

EAST Search History

L11	0	((semiconductor adj device) and ((gate adj electrode) with (well)) and ((well adj region) with channel) and (side with (island-shaped)) and (surface with well) and ((electrical adj connect$3) with gate with well)).clm.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/18 16:15
L12	2	((semiconductor adj device) and ((gate adj electrode) with (well)) and ((well adj region) with channel) and (side with (island-shaped)) and (surface with well) and ((electrical adj connect$3) with gate with well))	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/18 16:16
L13	1685	Yagishita.in.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/18 16:17
L14	106	13 and gate and semiconductor	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/18 16:17